Induced Effective Charge Balance CdSe/ZnS QDs based Light-Emitting Devices using PVP-encapped ZnO Nanoparticles

Ok-Sik Kim¹, Byoung-Ho Kang², Sang-Won Lee³, Jae-Sung Lee³, Seung-Hwan Cha³, Jun-Woo Lee³ and Shin-Won Kang³

¹Department of Sensor and Display Engineering, Kyungpook National University, Daegu 702-701, Republic of Korea
²Center for Functional Devices Fusion Platform, Kyungpook National University, Daegu 702-701, Republic of Korea
³School of Electronics Engineering, College of IT Engineering, Kyungpook National University, Daegu 702-701, Republic of Korea
Tel.: 82-53-950-6829, E-mail: swkang@knu.ac.kr

In recent years, several researchers have studied about the quantum dots based light-emitting devices (QDLEDs) because QDLEDs have many attractive characteristics, such as extremely narrow emission spectral bandwidth, luminescence efficiency, wide absorption and saturated colors [1]. Until now, many researchers have attempted to enhance the performance of QDLEDs, including the development of novel QDs and high transportation rate materials, designing the unique device structures, and the optimization of charge transport layer. Furthermore, metal oxide nanoparticles (NPs) such as TiO2 NPs, Al-doped ZnO NPs and NiO NPs have been used as charge transport layers in QD-LEDs to improve the luminance and efficiency. However, these materials have shown high efficiency but does not discussed QDLEDs performance corresponding to the oxygen vacancy [2].

In order to verify the effect of oxygen vacancy control, we synthesized the surface modulated ZnO NPs with polyvinyl pyrrolidone (PVP) by using sol-gel process. The QDLEDs with PVP-encapsulated ZnO NPs as electron transport layer showed significantly enhanced luminance and current efficiency due to the reduced trap density existed on the surface of ZnO NPs [3]. The bare ZnO based QDLEDs was showed the luminance of 23,570 cd/m² and current efficiency of 2.04 cd/A. On the other hand, PVP-encapsulated ZnO based QDLEDs was showed luminance of 33,420 cd/m² and current efficiency of 2.84 cd/A. Therefore, we confirmed that oxygen vacancy of ZnO NPs is very essential parameter for effective electron transportation.

![Fig. 1. Schematic diagram of (a) molecular structure of bare-ZnO NPs and pvp-capped ZnO NPs, (b) energy band diagram of QDLED, and results of (c) luminance and (d) current efficiency](image)

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**References**